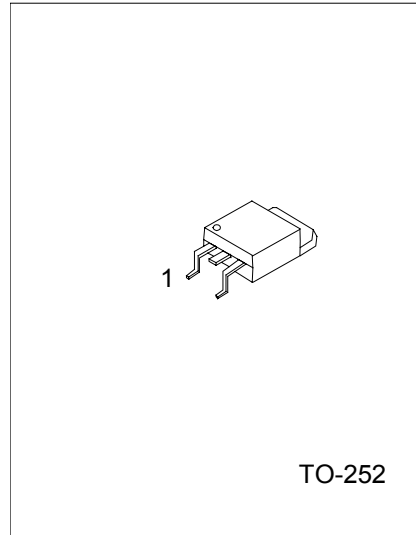


## HIGH VOLTAGE DRIVER APPLICATION

### FEATURES

- \*High breakdown voltage.
- \*Excellent hFE linearity.



TO-252

1: BASE 2:COLLECTOR 3:EMITTER

### ABSOLUTE MAXIMUM RATINGS ( Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CB0</sub>	-400	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-400	V
Emitter-Base Voltage	V <sub>EB0</sub>	-5	V
Collector Current	I <sub>c</sub>	-200	mA
Collector Current (PULSE)	I <sub>cp</sub>	-400	mA
Collector Power Dissipation	P <sub>c</sub>	1	W
		10( T <sub>c</sub> =25°C)	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 ~ +150	°C

### ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV <sub>CB0</sub>	I <sub>C</sub> = -10μA, I <sub>E</sub> =0	-400			V
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> = -1mA, I <sub>B</sub> =0, R <sub>BE</sub> =∞	-400			V
Emitter-Base Breakdown Voltage	BV <sub>EB0</sub>	I <sub>E</sub> = -10μA, I <sub>C</sub> =0	-5			V
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = -300V, I <sub>E</sub> =0			-0.1	μA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> = -4V, I <sub>C</sub> =0			-0.1	μA
DC Current Transfer Ratio	h <sub>FE</sub>	V <sub>CE</sub> = -10V, I <sub>c</sub> = -50mA	60		200	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -50mA, I <sub>B</sub> = -5mA			-0.8	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -50mA, I <sub>B</sub> = -5mA			-1.0	V
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -30V, f=1MHz		5		pF
Reverse Transfer Capacitance	C <sub>re</sub>	V <sub>CB</sub> = -30V, f=1MHz		4		pF

# UTC2SA1700

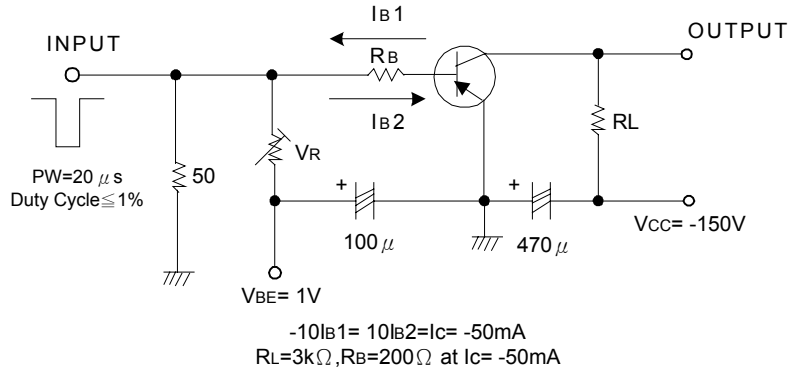
# PNP EPITAXIAL SILICON TRANSISTOR

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Gain-Bandwidth Product	$f_r$	$V_{CE} = -30V, I_c = -10mA$		70		MHz
Turn-on Time	$t_{on}$	See test circuit		0.25		$\mu s$
Turn-off Time	$t_{off}$	See test circuit		5		$\mu s$

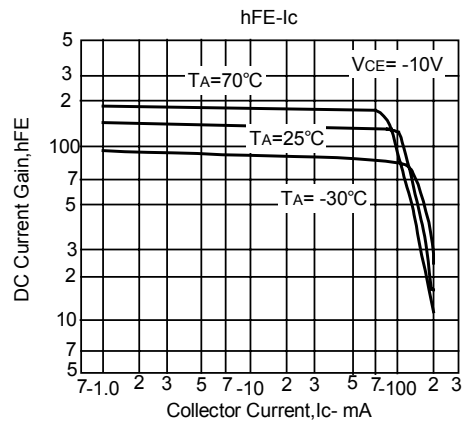
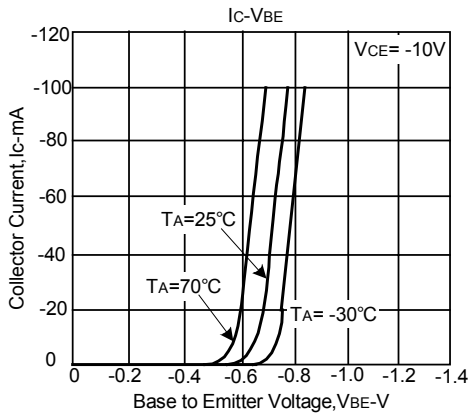
## CLASSIFICATION OF $h_{FE}$

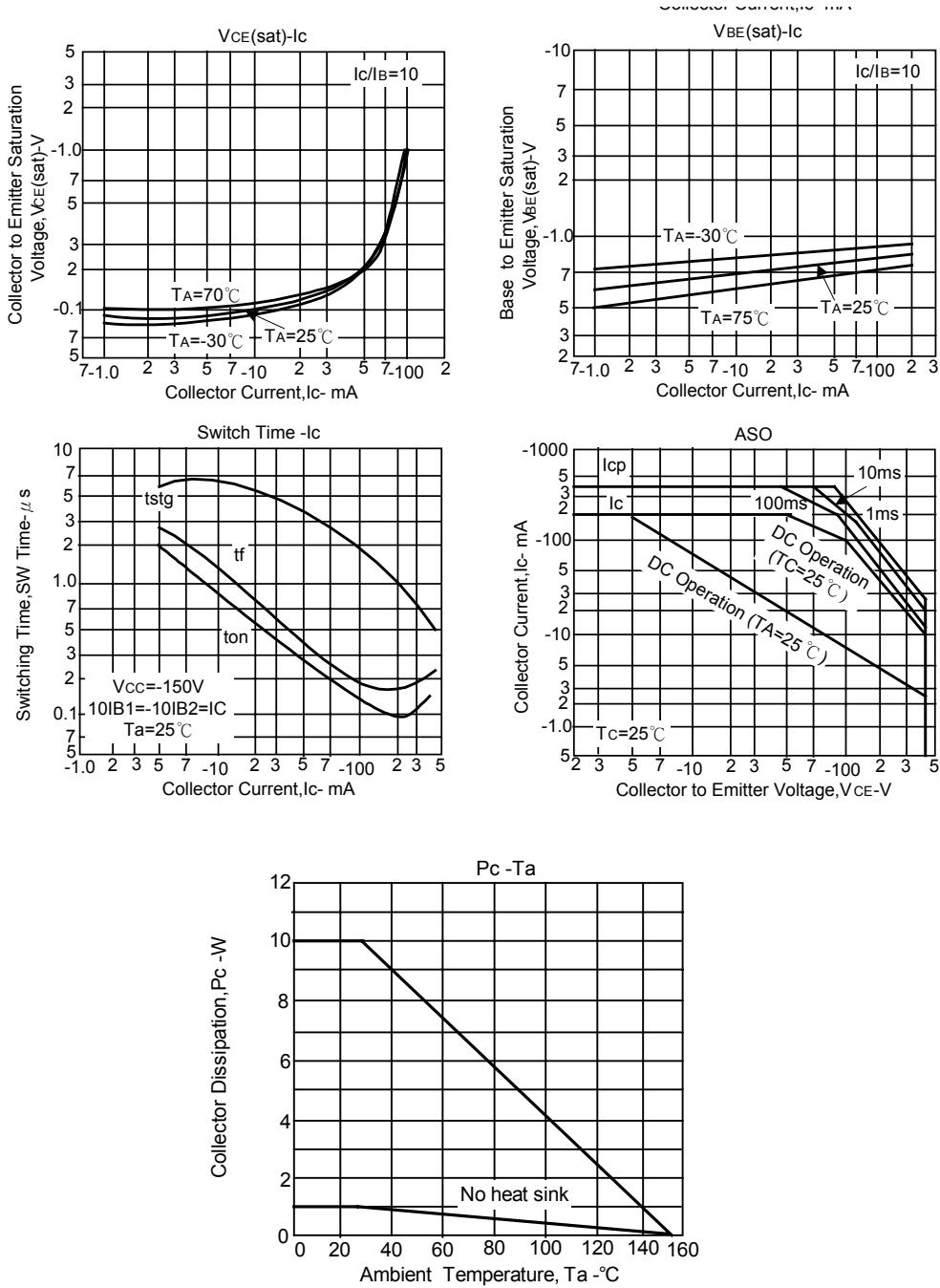
RANK	D	E
RANGE	60-120	100-200

TEST CIRCUIT (Unit : (resistance :  $\Omega$ , capacitance : F))



## ELECTRICAL CHARACTERISTICS CURVES





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